Ordering number : ENN7039

P-Channel Silicon MOSFET

MCH6607

Ultrahigh-Speed Switching Applications

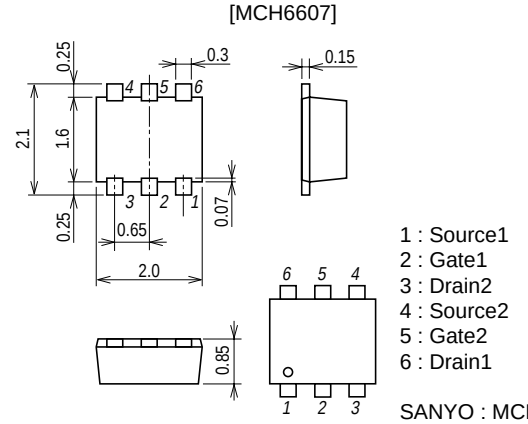
Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.
- Composite type with 2 MOSFETs contained in a single package, facilitaing high-density mounting.

Package Dimensions

unit : mm

2173A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−30	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		−0.4	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−1.6	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm)1unit	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0	−30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−30V, V_{GS}=0			−10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=−10V, I_D=−100μA	−0.4		−1.4	V
Forward Transfer Admittance	|yfs|	V_{DS}=−10V, I_D=−100mA	210	300		mS
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=−100mA, V_{GS}=−4V		2.4	3.1	Ω
	R_{DS}(on)2	I_D=−50mA, V_{GS}=−2.5V		3.5	4.9	Ω
	R_{DS}(on)3	I_D=−10mA, V_{GS}=−1.5V		10	20	Ω

Marking : FG

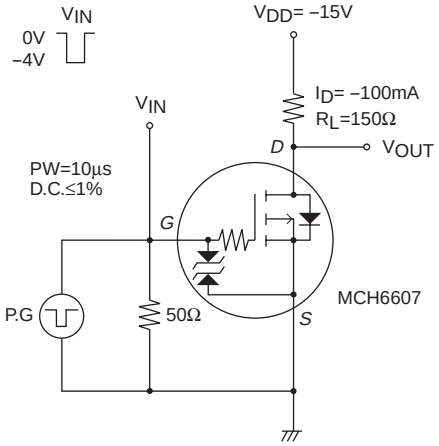
Continued on next page.

SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

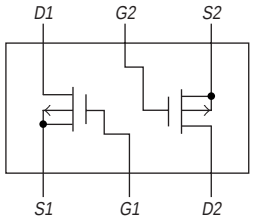
Continued from preceding page.

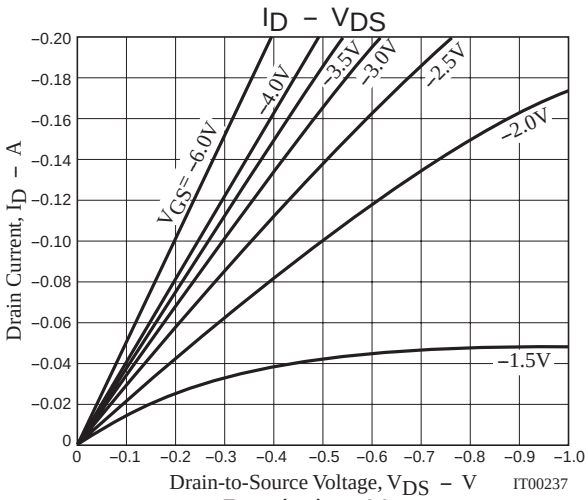
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		28		pF
Output Capacitance	Coss	V_{DS}=–10V, f=1MHz		15		pF
Reverse Transfer Capacitance	Crss	V_{DS}=–10V, f=1MHz		5.2		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		24		ns
Rise Time	t_{r}	See specified Test Circuit.		75		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit.		200		ns
Fall Time	t_{f}	See specified Test Circuit.		150		ns
Total Gate Charge	Qg	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–200mA		2		nC
Gate-to-Source Charge	Qgs	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–200mA		0.25		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–200mA		0.35		nC
Diode Forward Voltage	V_{SD}	I_{S}=–200mA, V_{GS}=0		–0.82	–1.2	V

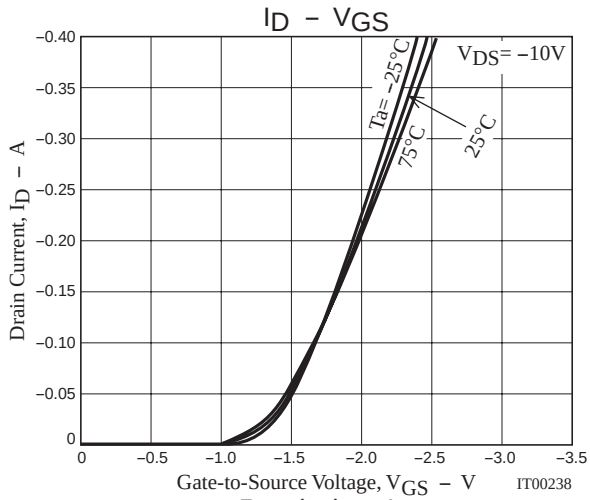
Switching Time Test Circuit

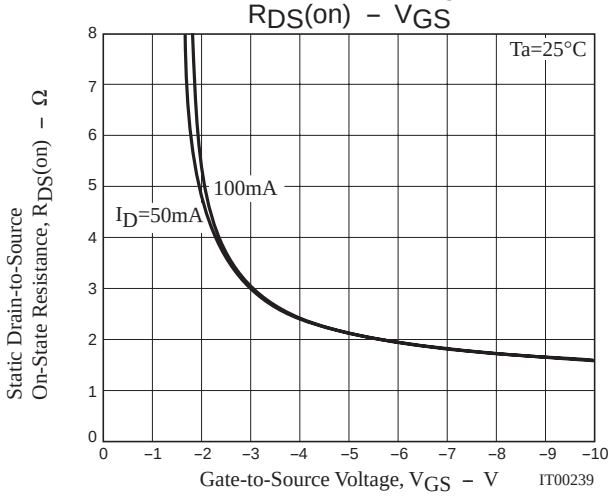


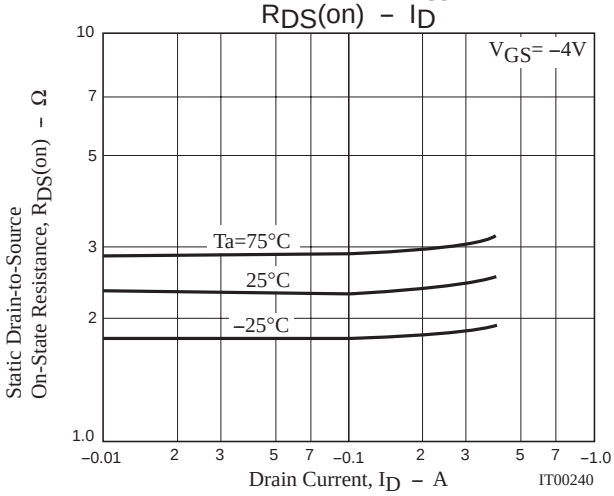
Electrical Connection

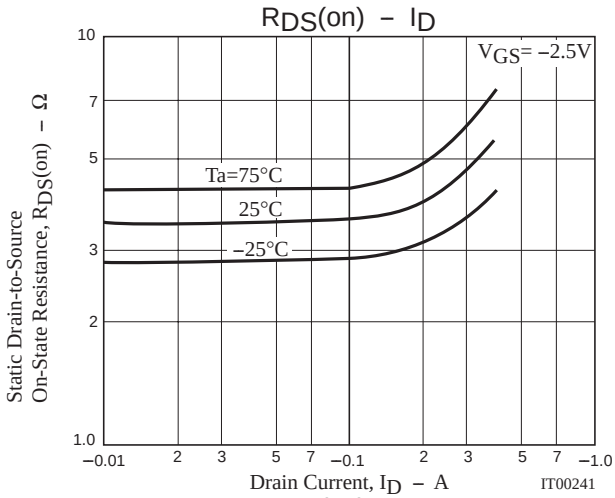


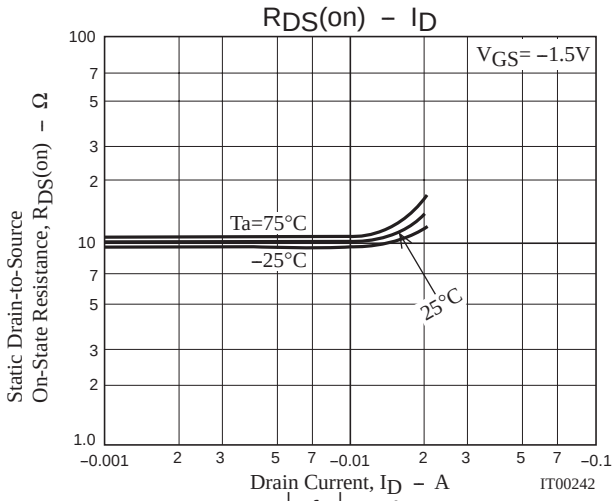


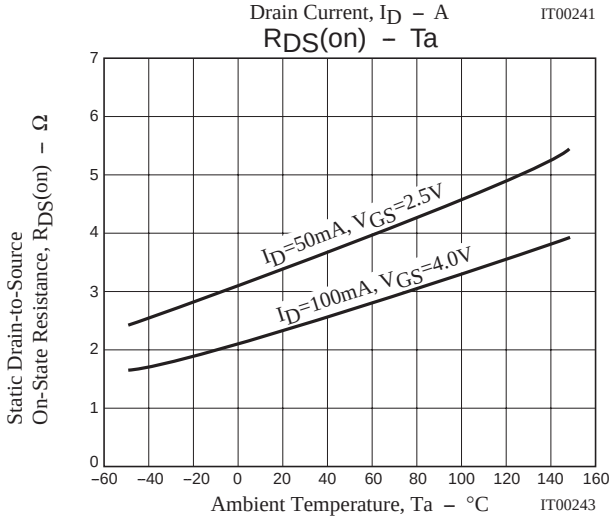


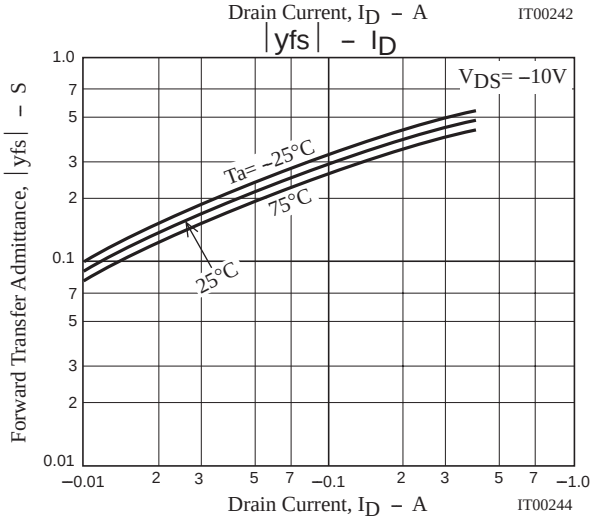


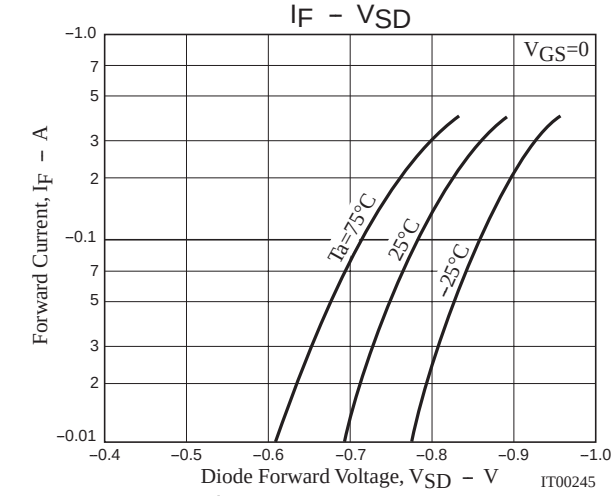


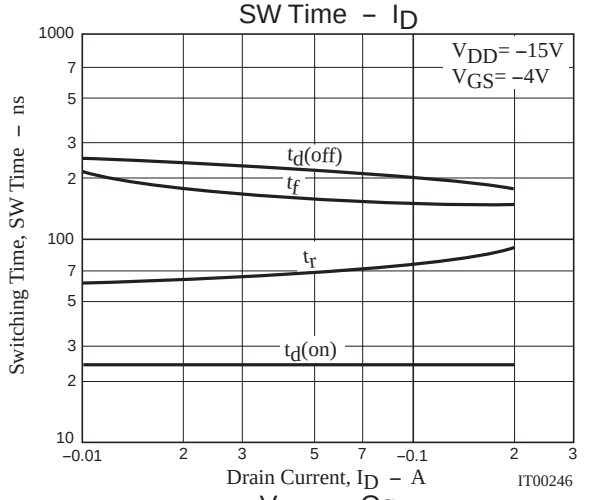

RDS(on) – ID
VGS= –2.5V
Ta=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00241

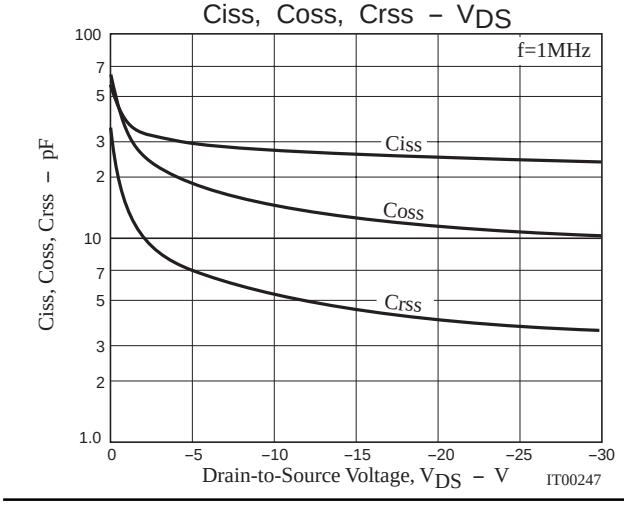

RDS(on) – ID
VGS= –1.5V
Ta=75°C
–25°C
25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00242

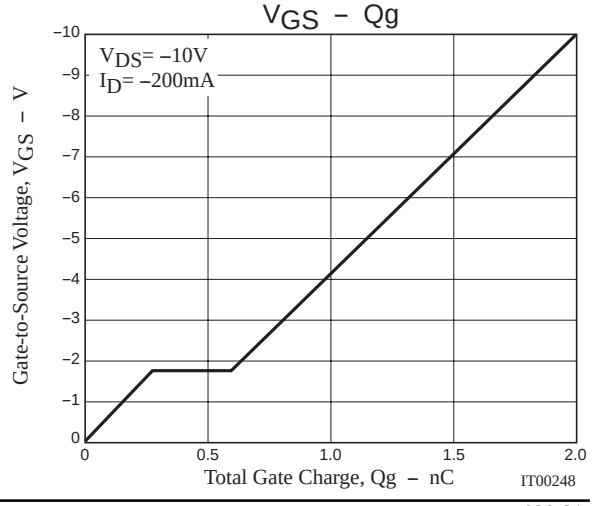

RDS(on) – Ta
ID=50mA, VGS=2.5V
ID=100mA, VGS=4.0V
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Ambient Temperature, Ta – °C
IT00243

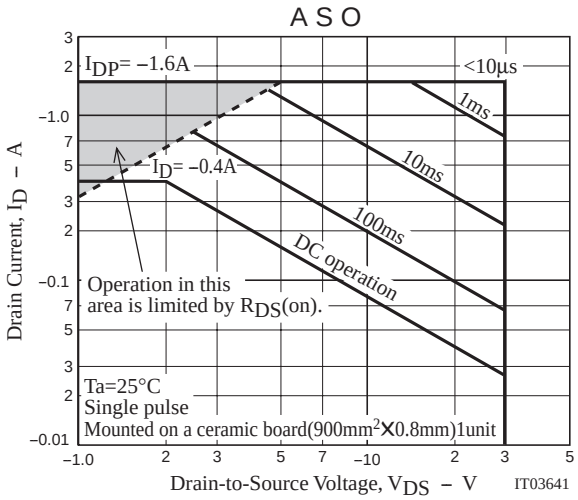

|yfs| – ID
VDS= –10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT00244

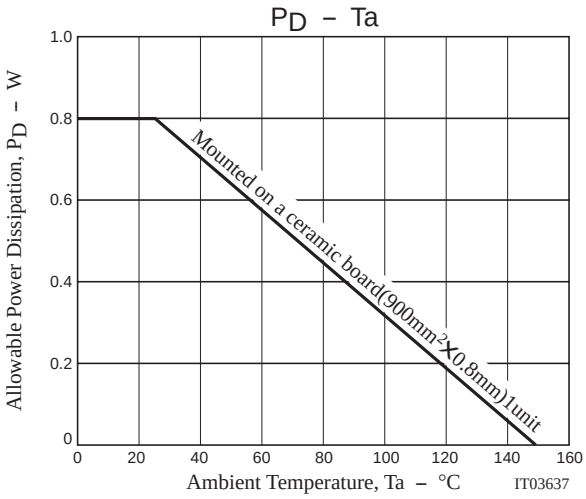

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT00245


SW Time – ID
VDD= –15V
VGS= –4V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT00246


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT00247


VGS – Qg
VDS= –10V
ID= –200mA
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT00248





Note on usage : Since the MCH6607 is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.